



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BVsss	Rss(on) Typ	Is _{Max} T _A = +25°C
12V	$3.4 \text{m}\Omega$ @ V _{GS} = 3.8V	19.2A

Description

This new generation MOSFET is designed to minimize the on-state resistance (Rss(on)) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

Applications

- Battery managements
- Load switches
- Battery protections

Features

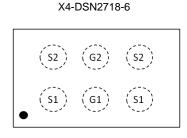
- CSP with Footprint 2.70mm x 1.81mm
- Height = 0.12mm for Low Profile
- ESD Protection of Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

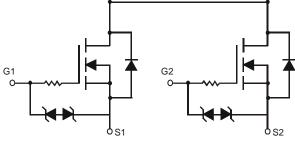
 https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: X4-DSN2718-6
- Terminal Connections: See Diagram Below
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiAu. Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.0026 grams (Approximate)







Top View

Equivalent Circuit

Ordering Information (Note 4)

Part Number	Paakaga	Pack	king
	Package	Qty.	Carrier
DMN16M7UCA6-7	X4-DSN2718-6	3000	Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



OJ = Product Type Marking Code YW = Date Code Marking Y or \overline{Y} = Year (ex: 3 = 2023) W or \overline{W} = Week (ex: a =week 27; z represents week 52 and 53)

Date Code Key

Year	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034
Code	3	4	5	6	7	8	9	0	1	2	3	4
Week 1-26						27-	-52			5	3	
Code	de A-Z				а	-Z			:	Z		



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit			
Source-Source Voltage	Vsss	12	V			
Gate-Source Voltage			V_{GSS}	±8	V	
Gate-Source Voltage (Note 5)	Vgss	±10.5	V			
Continuous Course Current (Note C) // A F)/	Steady State	T _A = +25°C	Is	19.2	А	
Continuous Source Current (Note 6) V _{GS} = 4.5V		T _A = +70°C		15.4		
Continuous Course Current (Note C) Vos. 2 5V	Steady	T _A = +25°C	1-	15.9	۸	
Continuous Source Current (Note 6) Vgs = 2.5V	State	T _A = +70°C	Is	12.8	Α	
Pulsed Source Current (Note 7)	Ism	85	А			

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 8)	PD	1.0	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 8)	Reja	128.2	°C/W
Power Dissipation (Note 6)	PD	2.1	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 6)	Reja	58.4	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

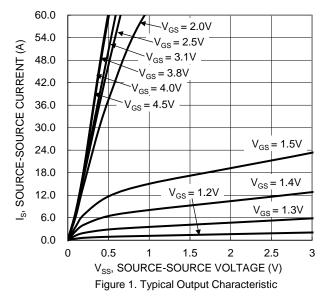
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

			_			A
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Source-Source Breakdown Voltage	BV _{SSS}	12	_	_	V	$V_{GS} = 0V$, $I_S = 1mA$
Zero Gate Voltage Drain Current, T _J = +25°C	Isss		_	1	μA	Vss = 10V, Vgs = 0V
Gate-Source Leakage	Igss	_	_	±10	μΑ	$V_{GS} = \pm 8V$, $V_{SS} = 0V$
Gale-Gource Leakage	I _{GSS}	_	_	±1	μΑ	$V_{GS} = \pm 5V$, $V_{SS} = 0V$
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	0.5	0.7	1.3	V	Vss = 6V, Is = 1mA
		2.4	3.3	3.8		V _G S = 4.5V, I _S = 3A
Static Source-Source On-Resistance	D	2.5	3.4	4.0	mΩ	V _G S = 3.8V, I _S = 3A
Static Source-Source On-Resistance	R _{SS(ON)}	2.8	3.6	4.5		V _{GS} = 3.1V, I _S = 3A
		3.0	4.1	5.5		V _G S = 2.5V, I _S = 3A
Diode Forward Voltage	Vss	_	0.7	1.2	V	$V_{GS} = 0V$, $I_{S} = 3A$
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	Ciss	_	2333	_		V 0V V 0V
Output Capacitance	Coss		743	_	pF	Vss = 6V, $Vgs = 0V$, f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	175	_		1 = 1.000112
Total Gate Charge	Qg	_	45.4	_		
Gate-Source Charge	Qgs	_	10.6	_	nC	$V_{SS} = 6V, V_{GS} = 4.5V,$
Gate-Drain Charge	Qgd	_	9.6	_	nc nc	I _S = 18A
Gate Charge at V⊤н	Q _g (TH)	_	6.2	_		
Turn-On Delay Time	t _D (ON)	_	0.4	_		
Turn-On Rise Time	t _R	_	1.7	_		$V_{SS} = 6V, V_{GS} = 4.5V,$
Turn-Off Delay Time	tD(OFF)	_	6.8	_	ns	Is = 3A
Turn-Off Fall Time	tF	_	4.7	_		

Notes:

- 5. $t = 10\mu s$, Duty Cycle $\leq 1\%$.
- 6. Device mounted on FR-4 material with 1inch² (6.45cm²), 2oz. (0.071mm thick) Cu.
- 7. Repetitive rating, pulse width limited by junction temperature.8. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to production testing.





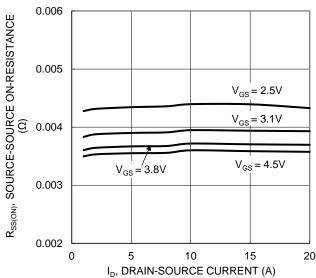


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

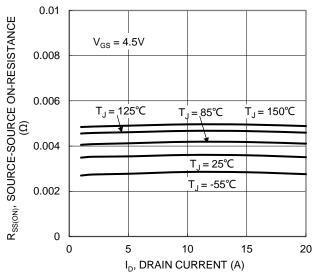
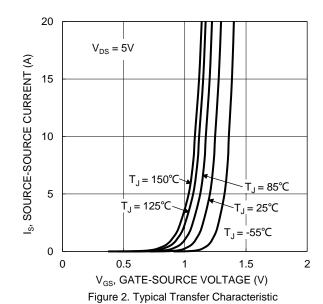
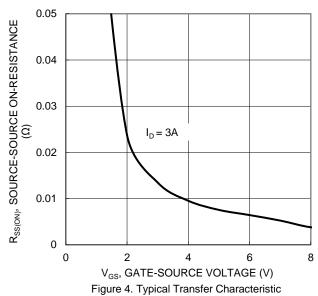


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





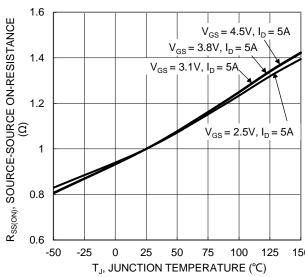


Figure 6. On-Resistance Variation with Temperature



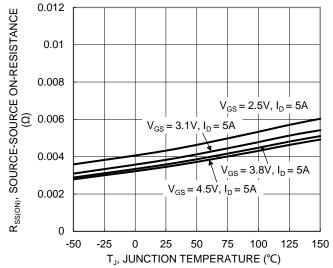
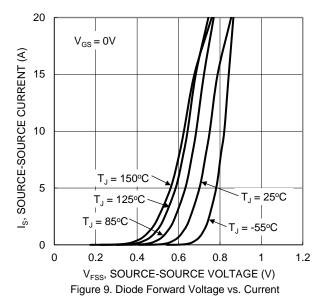
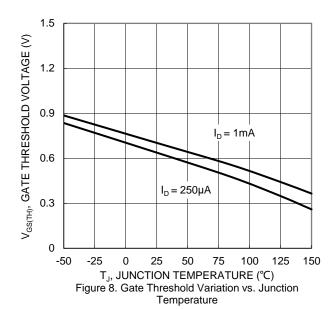


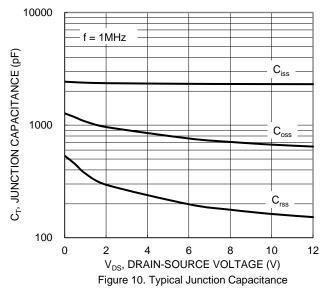
Figure 7. On-Resistance Variation with Temperature

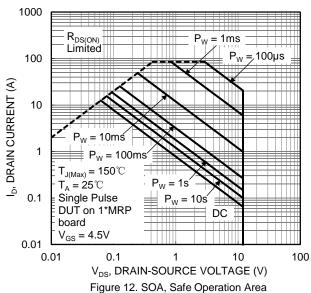


9.6 8.4 7.2 6 $V_{GS}(V)$ 3.6 $V_{SS} = 6V, I_{S} = 18A$ 2.4 1.2 0 12 48 0 24 60 72 84 96 Q_q (nC)

Figure 11. Gate Charge









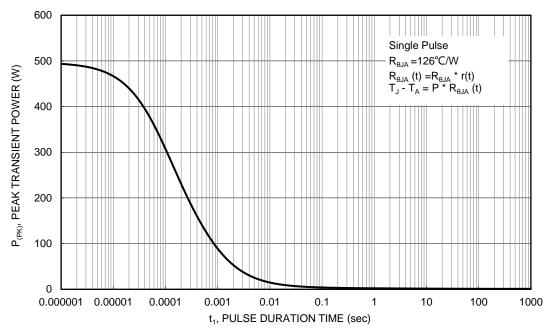


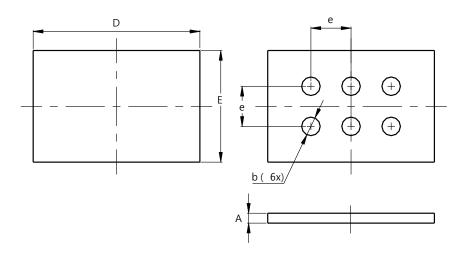
Figure 13. Single Pulse Maximum Power Dissipation



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X4-DSN2718-6

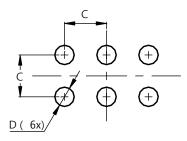


X4-DSN2718-6							
Dim	Min	Max	Тур				
Α	0.085	0.16	0.11				
b	0.27	0.33	0.30				
D	2.65	2.75	2.70				
Е	1.76	1.86	1.81				
е	0.62	0.68	0.65				
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X4-DSN2718-6



Dimensions	Value (in mm)			
C	0.65			
D	0.30			



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